

# PUMD2

# 50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 22 k $\Omega$ , R2 = 22 k $\Omega$

1 April 2023

**Product data sheet** 

### 1. General description

NPN/PNP Resistor-Equipped double Transistor (RET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

NPN/NPN complement: PUMH1 PNP/PNP complement: PUMB1

### 2. Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- · Reduces component count
- Reduces pick and place costs

# 3. Applications

- · Low current peripheral driver
- Controlling IC inputs
- · Replaces general-purpose transistors in digital applications

#### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor	Per transistor						
V <sub>CEO</sub>	collector-emitter voltage	open base	[1]	-	-	50	V
Io	output current		[1]	-	-	100	mA
R1	bias resistor 1 (input)		[2]	15.4	22	28.6	kΩ
R2/R1	bias resistor ratio		[2]	0.8	1	1.2	

- [1] For the PNP transistor with negative polarity.
- [2] See section "Test information" for resistor calculation and test conditions.



# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1		O1 I2 GND2
2	l1	input (base) TR1		
3	O2	output (collector) TR2	6 5 4	R1 R2
4	GND2	GND (emitter) TR2		TR2
5	12	input (base) TR2		TR1 R2 R1
6	O1	output (collector) TR1	☐1 ☐2 ☐3 TSSOP6 (SOT363)	GND1 I1 O2 006aaa143

# 6. Ordering information

**Table 3. Ordering information** 

Type number	Package		
	Name	Description	Version
PUMD2		plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	<u>SOT363</u>

# 7. Marking

#### Table 4. Marking codes

Type number	Marking code[1]
PUMD2	D%2

[1] % = placeholder for manufacturing site code

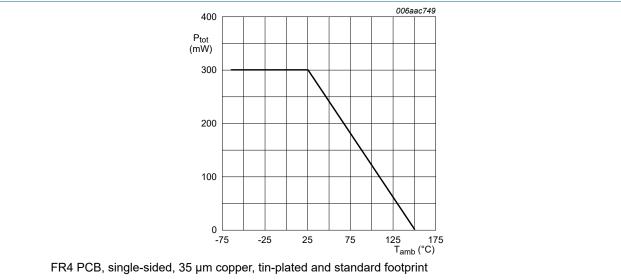
# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transisto	or					_
V <sub>CBO</sub>	collector-base voltage	open emitter	[1]	-	50	V
$V_{CEO}$	collector-emitter voltage	open base	[1]	-	50	V
$V_{EBO}$	emitter-base voltage	open collector	[1]	-	10	V
VI	input voltage	TR1 (NPN)		-10	40	V
		TR2 (PNP)		-40	10	V
Io	output current		[1]	-	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[2]	-	200	mW
Per device			,	,		
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[2]	-	300	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- [1] For the PNP transistor with negative polarity.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided, 35 µm copper, tin-plated and standard footprint.



50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 22 k $\Omega$ , R2 = 22 k $\Omega$ 

### 9. Thermal characteristics

#### **Table 6. Thermal characteristics**

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	625	K/W
Per device							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	417	K/W

[1] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint.

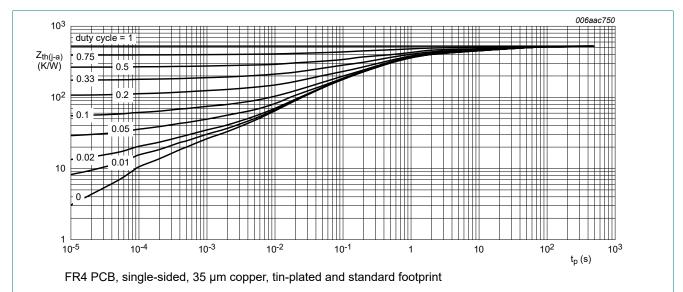


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 22 k $\Omega$ , R2 = 22 k $\Omega$ 

# 10. Characteristics

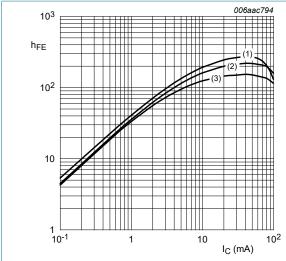
#### **Table 7. Characteristics**

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transisto	or						
V <sub>(BR)CBO</sub>	collector-base breakdown voltage	$I_C = 100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$	[1]	50	-	-	V
V <sub>(BR)CEO</sub>	collector-emitter breakdown voltage	$I_C = 2 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$	[1]	50	-	-	V
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = 50 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	[1]	-	-	100	nA
I <sub>CEO</sub>	collector-emitter cut-off	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0 A; T <sub>amb</sub> = 25 °C	[1]	-	-	100	nA
	current	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0 A; T <sub>j</sub> = 150 °C	[1]	-	-	5	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$I_{EB} = 5 \text{ V}; I_{C} = 0 \text{ mA}; T_{amb} = 25 \text{ °C}$		-	-	180	μA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 5 mA; T <sub>amb</sub> = 25 °C	[1]	60	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$_{\rm C}$ = 10 mA; $I_{\rm B}$ = 0.5 mA; $T_{\rm amb}$ = 25 °C		-	-	150	mV
$V_{I(off)}$	off-state input voltage	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 100 μA; T <sub>amb</sub> = 25 °C	[1]	-	1.1	0.8	V
V <sub>I(on)</sub>	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 5 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$		2.5	1.7	-	V
R1	bias resistor 1 (input)		[2]	15.4	22	28.6	kΩ
R2/R1	bias resistor ratio		[2]	0.8	1	1.2	
TR1 (NPN)	'				'		
C <sub>c</sub>	collector capacitance	$V_{CB}$ = 10 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; f = 1 MHz; $T_{amb}$ = 25 °C		-	-	2.5	pF
f <sub>T</sub>	transition frequency	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA}; f = 100 \text{ MHz};$ $T_{amb} = 25 \text{ °C}$	[3]	-	230	-	MHz
TR2 (PNP)							
C <sub>c</sub>	collector capacitance	$V_{CB}$ = -10 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; $f$ = 1 MHz; $T_{amb}$ = 25 °C		-	-	3	pF
f <sub>T</sub>	transition frequency	$V_{CE}$ = -5 V; $I_{C}$ = -10 mA; f = 100 MHz; $T_{amb}$ = 25 °C	[3]	-	180	-	MHz

<sup>[1]</sup> For the PNP transistor with negative polarity.

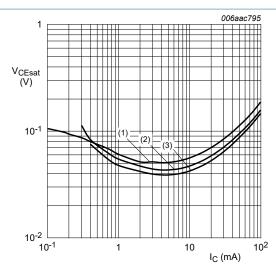
<sup>[2]</sup> See section "Test information" for resistor calculation and test conditions.

<sup>[3]</sup> Characteristics of built-in transistor



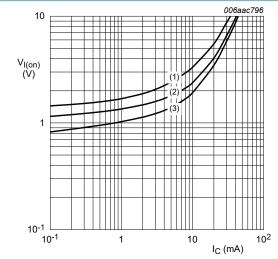
V<sub>CE</sub> = 5 V (1) T<sub>amb</sub> = 100 °C (2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = -40 °C

TR1 (NPN): DC current gain as a function of Fig. 3. collector current; typical values



 $I_{C}/I_{B} = 20$ (1)  $T_{amb} = 100 \, ^{\circ}C$ (2)  $T_{amb} = 25 \, ^{\circ}C$ (3)  $T_{amb} = -40 \, ^{\circ}C$ 

Fig. 4. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values



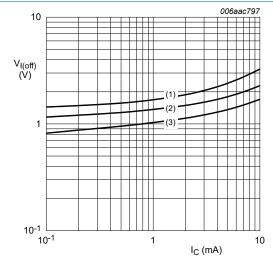
 $V_{CE} = 0.3 V$ 

(1)  $T_{amb}$  = -40 °C

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig. 5. TR1 (NPN): On-state input voltage as a function | Fig. 6. of collector current; typical values



 $V_{CE} = 5 V$ 

(1)  $T_{amb} = -40 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

TR1 (NPN): Off-state input voltage as a function of collector current; typical values

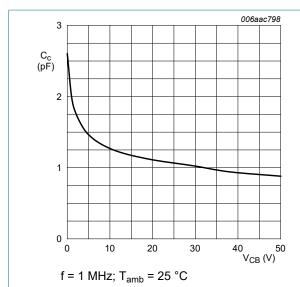
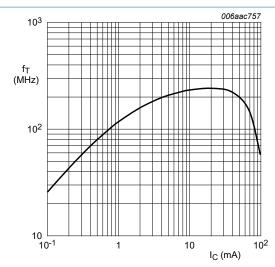
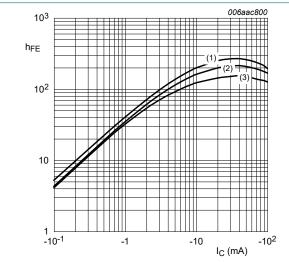


Fig. 7. TR1 (NPN): Collector capacitance as a function of collector-base voltage; typical values



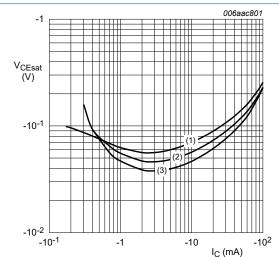
f = 100 MHz  $T_{amb} = 25 \text{ °C}$   $V_{CE} = 5 \text{ V}$ 

Fig. 8. TR1 (NPN): Transition frequency as a function of collector current; typical values of built-in transistor



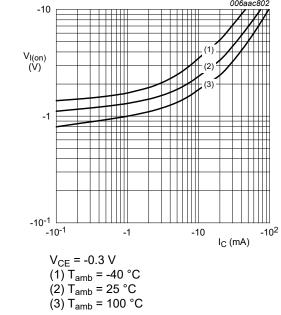
 $V_{CE} = -5 V$ (1)  $T_{amb} = 100 \,^{\circ}C$ (2)  $T_{amb} = 25 \,^{\circ}C$ (3)  $T_{amb} = -40 \,^{\circ}C$ 

Fig. 9. TR2 (PNP): DC current gain as a function of collector current; typical values



 $I_C/I_B = 20$ (1)  $T_{amb} = 100 \,^{\circ}C$ (2)  $T_{amb} = 25 \,^{\circ}C$ (3)  $T_{amb} = -40 \,^{\circ}C$ 

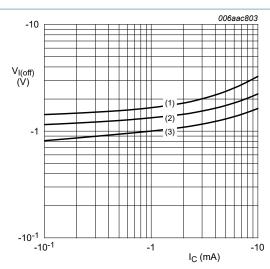
Fig. 10. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values



$$(1) T_{amb} = -40 ° ($$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

of collector current; typical values

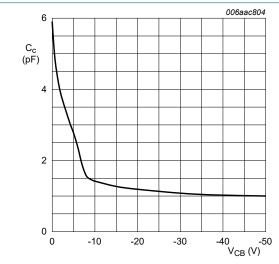


$$V_{CE} = -5 V$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

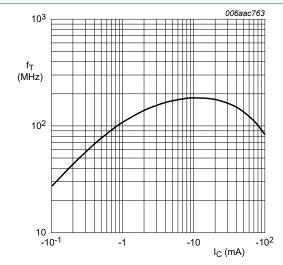
(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig. 11. TR2 (PNP): On-state input voltage as a function | Fig. 12. TR2 (PNP): Off-state input voltage as a function of collector current; typical values



 $f = 1 MHz; T_{amb} = 25 °C$ 

Fig. 13. TR2 (PNP): Collector capacitance as a function of collector-base voltage; typical values



f = 100 MHz

 $T_{amb}$  = 25 °C

 $V_{CE} = -5 V$ 

Fig. 14. TR2 (PNP): Transition frequency as a function of collector current; typical values of built-in transistor

# 11. Test information

#### **Resistor calculation**

• Calculation of bias resistor 1 (R1)

$$R_{I} = \frac{V(I_{2}) - V(I_{1})}{I_{2} - I_{1}}$$

· Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I4) - V(I3)}{R1 \cdot (I4 - I3)} - 1$$

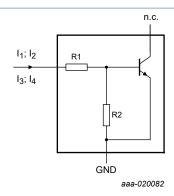


Fig. 15. TR1 (NPN): Resistor test circuit

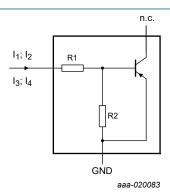


Fig. 16. TR2 (PNP): Resistor test circuit

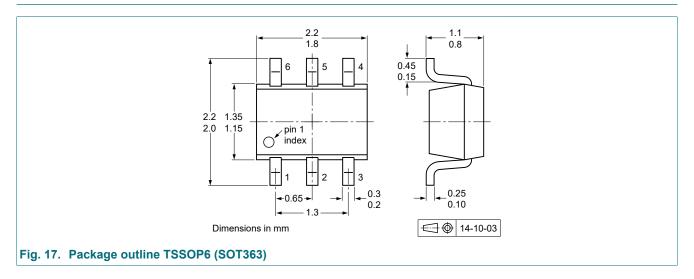
#### **Resistor test conditions**

**Table 8. Resistor test conditions** 

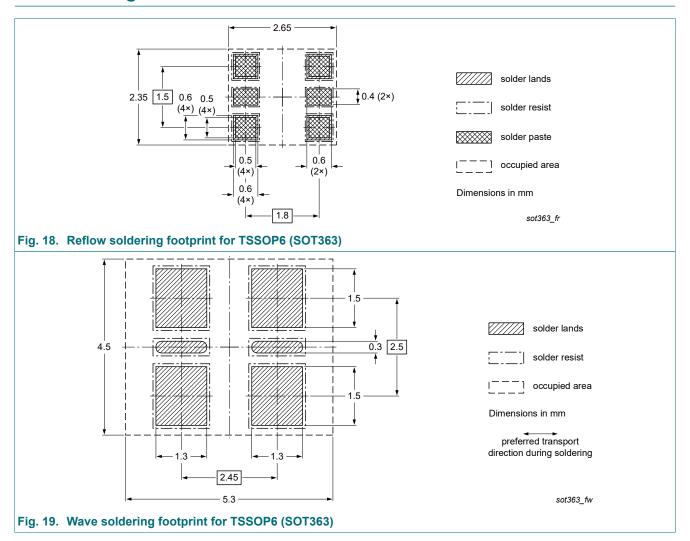
PUMD2	R1 (kΩ)	R2 (kΩ)	Test conditions				
			I <sub>1</sub>	l <sub>2</sub>	l <sub>3</sub>	14	
TR1 (NPN)	22	22	150 μΑ	230 μΑ	-150 μA	-230 μA	
TR2 (PNP)	22	22	-150 μΑ	-230 µA	150 µA	230 μΑ	

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 22 k $\Omega$ , R2 = 22 k $\Omega$ 

# 12. Package outline



# 13. Soldering



50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 22 k $\Omega$ , R2 = 22 k $\Omega$ 

# 14. Revision history

#### Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes	
PUMD2 v.9	20230401	Product data sheet	-	PEMD2_PIMD2_PUMD2 v.8	
Modifications:	<ul> <li>The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia.</li> <li>Legal texts have been adapted to the new company name where appropriate.</li> <li>Product changed to non-automotive qualification. Please refer to nexperia.com for automotive (-Q) product alternative(s).</li> <li>Family data sheet splitted to single type data sheets.</li> </ul>				
PEMD2_PIMD2_PUMD2 v.8	20131114	Product data sheet	-	PEMD2_PIMD2_PUMD2 v.7	
PEMD2_PIMD2_PUMD2 v.7	20080924	Product data sheet	-	PEMD2_PIMD2_PUMD2 v.6	
PEMD2_PIMD2_PUMD2 v.6	20042104	Product specification	-	PEMD2_PIMD2_PUMD2 v.5	
PEMD2_PIMD2_PUMD2 v.5	20030606	Product specification	-	-	

#### 50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 22 k $\Omega$ , R2 = 22 k $\Omega$

### 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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